

# Schottky Barrier Diode

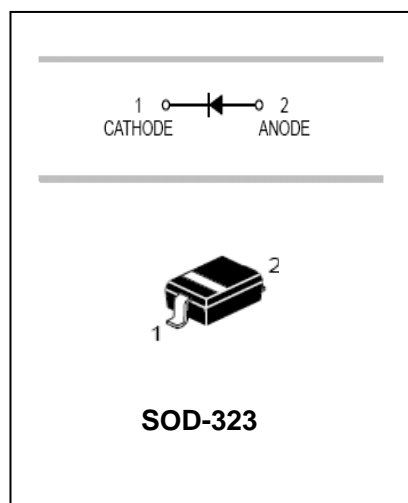
# SD103AWS/SD103BWS/SD103CWS

## FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction For Transient Protection
- Negligible Reverse Recovery Time
- Low Reverse Capacitance



Lead-free



## APPLICATIONS

- Schottky barrier switching

## ORDERING INFORMATION

Type No.	Marking	Package Code
SD103AWS	S4	SOD-323
SD103BWS	S5	SOD-323
SD103CWS	S6	SOD-323

## MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	SD103AWS	SD103BWS	SD103CWS	Unit
Peak Repetitive Peak reverse voltage	$V_{RRM}$				
Working Peak DC Reverse Voltage	$V_{RWM}$	40	30	20	V
	$V_R$				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Forward Continuous Current	$I_F$	350			mA
Repetitive Peak Forward Current @t≤1.0s	$I_{FSM}$	1.5			A
Power Dissipation	$P_d$	200			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625			°C/W
Storage temperature	$T_{stg}$	-65 to+125			°C



## Schottky Barrier Diode **SD103AWS/SD103BWS/SD103CWS**

### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	SD103AWS SD103BWS SD103CWS	40 30 20			V	$I_R=10\mu A$ $I_R=10\mu A$ $I_R=10\mu A$
Forward voltage	$V_F$			0.37 0.60	V	$I_F=20mA$ $I_F=200mA$
Reverse current	SD103AWS SD103BWS SD103CWS			5.0	$\mu A$	$V_R=30V$ $V_R=20V$ $V_R=10V$
Junction Capacitance	$C_J$		50		pF	$V_R=0, f=1MHz$
Reverse Recovery Time	$t_{rr}$		10		ns	$I_R=I_F=200mA$ $I_{rr}=0.1 \cdot I_R, R_L=100\Omega$

### TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

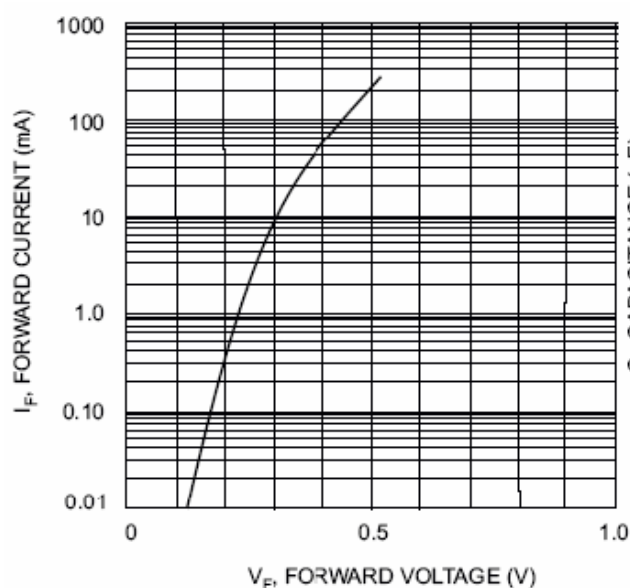


Fig. 1 Typical Forward Characteristics

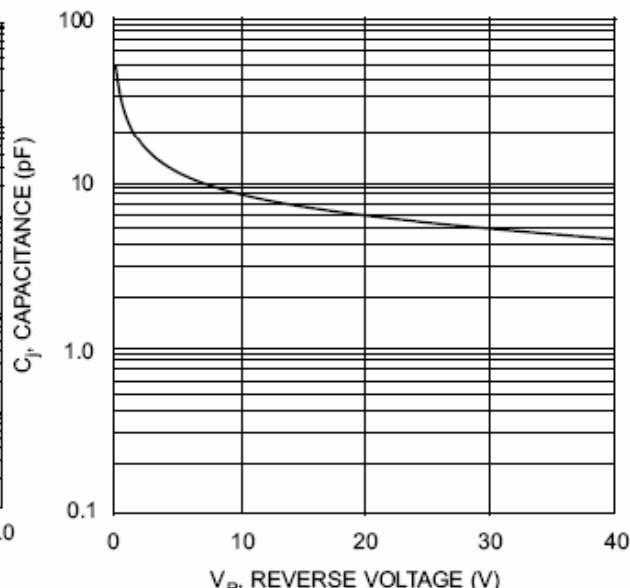


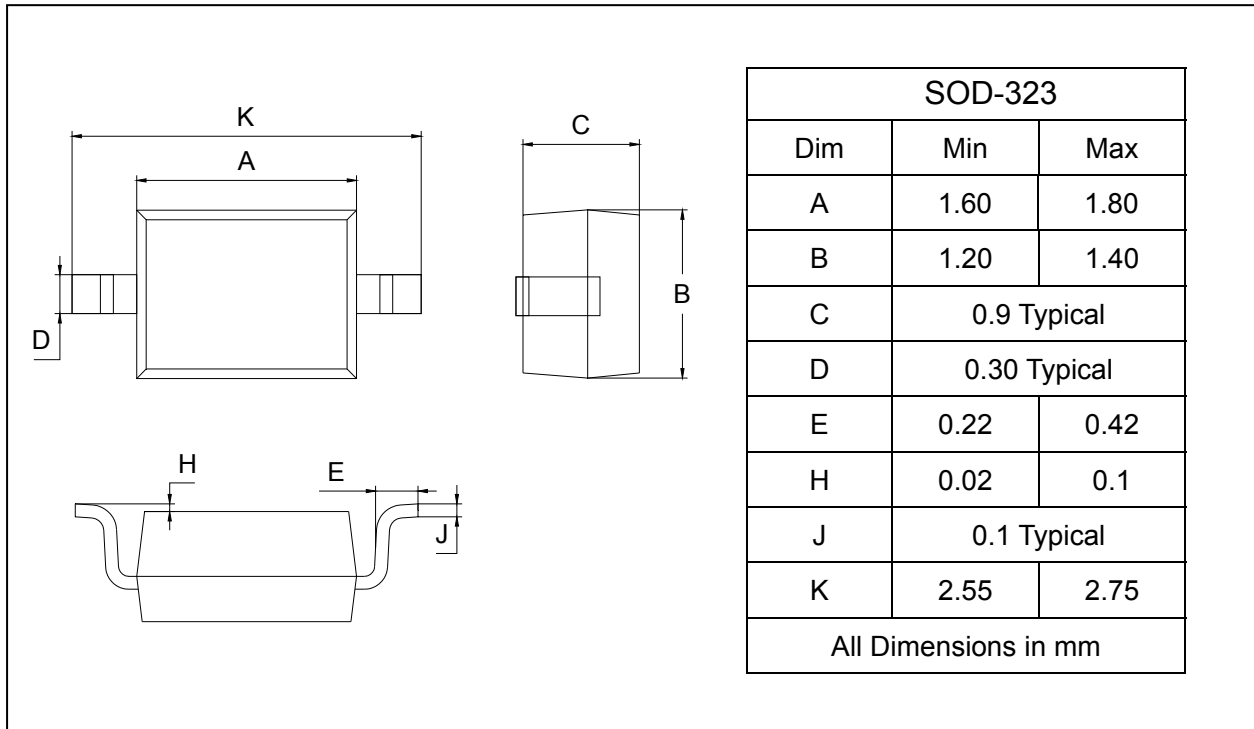
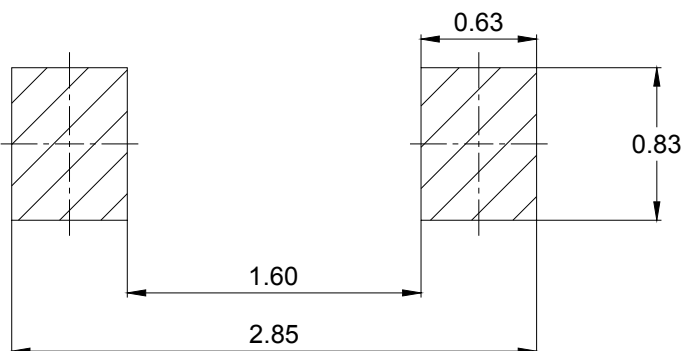
Fig. 2 Typ. Junction Capacitance vs Reverse Voltage

## Schottky Barrier Diode

**SD103AWS/SD103BWS/SD103CWS**
**PACKAGE OUTLINE**

Plastic surface mounted package

SOD-323


**SOLDERING FOOTPRINT**


Unit : mm

**PACKAGE INFORMATION**

Device	Package	Shipping
SD103AWS-SD103CWS	SOD-323	3000/Tape&Reel